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ABSTRACT OF THE DISCLOSURE

h3 A ~~film forming~~ method for forming a deposited film on a substrate ~~arranged in a substantially enclosed film-forming vessel by means of~~ via plasma CVD by introducing a ~~raw material gas comprising at least a~~ hydrogen gas and a silicon-containing raw material gas into a ~~said~~ film-forming vessel and introducing a high frequency power into the ~~said~~ film-forming vessel through a discharge electrode provided in the ~~said~~ film-forming vessel to generate a plasma in a plasma generation region between the ~~said~~ substrate and the ~~said~~ discharge electrode ~~in said film-forming vessel whereby forming to form a~~ said deposited film on the ~~said~~ substrate, ~~wherein the~~ The formation of the ~~said~~ deposited film ~~on said substrate~~ is performed while applying a periodicity voltage having at least two different waveform components having a different amplitude to an auxiliary electrode arranged at either (i) a position in the ~~said~~ plasma generation region ~~of said film-forming vessel or an auxiliary electrode provided~~ or (ii) on the rear side of the ~~said~~ substrate and outside the ~~said~~ plasma generation region.--

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